



Product data sheet

Product profile 1.

1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD59 (2-lead TO-220AC) plastic package.

1.2 Features

- Extremely fast switching Reduces switching loss in associated
- Low thermal resistance Low reverse recovery current
- MOSFET

1.3 Applications

■ Half-bridge or full-bridge switched-mode ■ Continuous Current Mode (CCM) Power Factor Correction (PFC) power supplies Half-bridge lighting ballasts

1.4 Quick reference data



V_F = 1.54 V (typ)

I_{F(AV)} ≤ 20 A ■ t_{rr} = 19 ns (typ)

2. **Pinning information**

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode (k)		
2	anode (a)	mb	k ————————————————————————————————————
mb	mounting base; cathode		

SOD59 (2-lead TO-220AC)



3. Ordering information

Table 2. Orderin	g information		
Type number	Package		
	Name	Description	Version
BYC20-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

4. Limiting values

Table 3.Limiting values

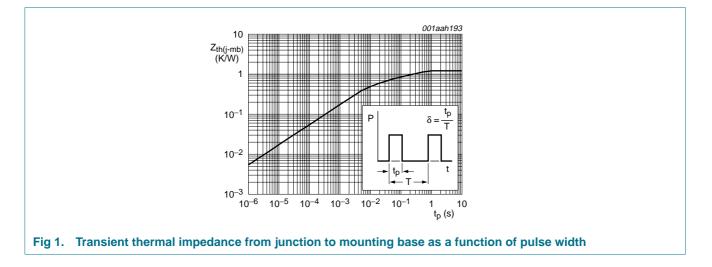
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	square waveform; δ = 1.0; T_{mb} \leq 100 $^{\circ}C$	-	500	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; T_{mb} \leq 93 $^{\circ}C$	-	20	А
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; T_{mb} \leq 93 °C; t_{p} = 25 μ s;	-	40	A
I _{FSM}	non-repetitive peak forward	t = 10 ms; sinusoidal waveform	-	250	А
	current	t = 8.3 ms; sinusoidal waveform	-	274	А
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

Rectifier diode, hyperfast

5. Thermal characteristics

Table 4.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; see <u>Figure 1</u>	-	-	1.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



Rectifier diode, hyperfast

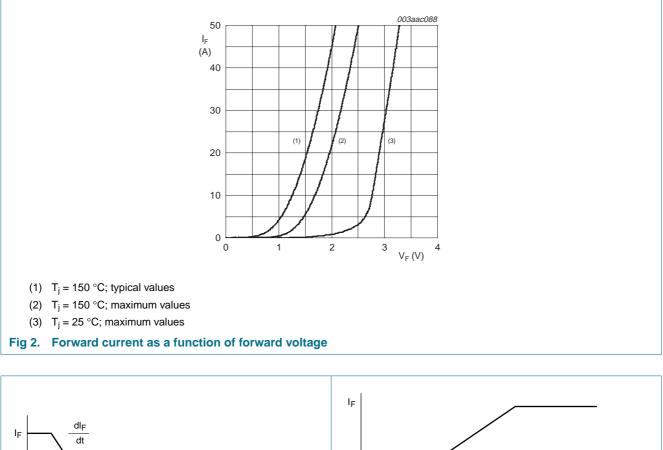
6. Characteristics

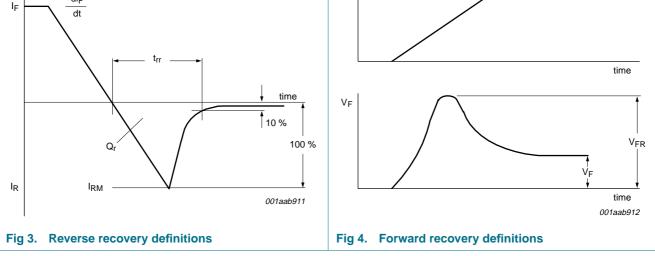
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
VF	forward voltage	$I_F = 20 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 2}}{\text{Figure 2}}$	-	1.54	1.97	V
		$I_F = 40 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 2}}{\text{Figure 2}}$	-	1.95	2.34	V
		I _F = 20 A; see <u>Figure 2</u>	-	1.89	2.9	V
R reverse current		V _R = 600 V	-	16	200	μA
		$V_R = 500 \text{ V}; \text{ T}_j = 100 ^{\circ}\text{C}$	-	1.6	3.0	mA
Dynamic o	haracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A to } V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ see Figure 3	-	35	55	ns
		I _F = 20 A to V _R = 400 V; dI _F /dt = 500 A/μs; see <u>Figure 3</u>				
		T _j = 25 °C	-	19	-	ns
		T _j = 100 °C	-	32	40	ns
I _{RM}	peak reverse recovery current	$I_F = 20 \text{ A to } V_R = 400 \text{ V}; T_j = 125 \text{ °C};$ see Figure 3				
		$dI_F/dt = 50 A/\mu s$	-	3.0	7.5	А
		$dI_F/dt = 500 \text{ A}/\mu \text{s}$	-	9.5	12	А
V _{FR}	forward recovery voltage	$I_F = 20 \text{ A}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ see Figure 4	-	8	11	V

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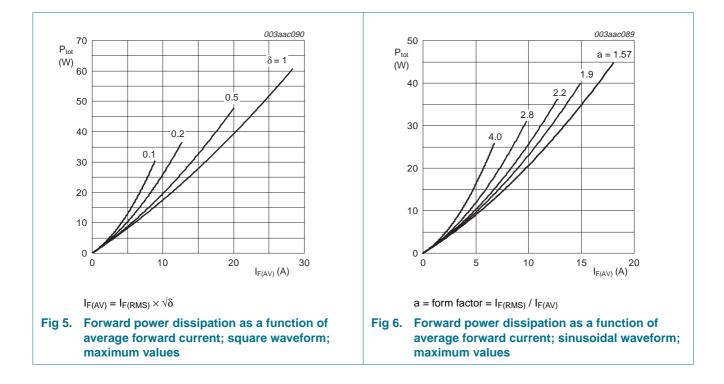




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7. Package outline

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		nm are ti						sca	ale			. (1)				7
UNIT	Α	A ₁	b	b1	С	D	D1	sca E	ale e	L	L ₁	L2 ⁽¹⁾	P 38	q	Q	_
		A 1 1.39	b 0.9	b 1 1.3	c 0.7		D1 6.4	E 10.3	ale	L 15.0	3.30	L ₂ ⁽¹⁾ 3.0	P 3.8 3.6	3.0	2.6	
UNIT mm Note	A 4.5 4.1	A ₁ 1.39 1.27	b 0.9 0.7	b1 1.3 1.0	c 0.7 0.4	D 15.8	D1	sca E	ale e	L			3.8			
UNIT mm Note I. Termi	A 4.5 4.1 nals in th	A 1 1.39	b 0.9 0.7	b1 1.3 1.0	c 0.7 0.4	D 15.8 15.2	D1 6.4 5.9	sca E 10.3 9.7	ale e	L 15.0	3.30		3.8 3.6	3.0 2.7	2.6 2.2	
UNIT mm Note 1. Termi	A 4.5 4.1	A ₁ 1.39 1.27	b 0.9 0.7	b ₁ 1.3 1.0 entrolled.	c 0.7 0.4	D 15.8 15.2	D1 6.4	sca E 10.3 9.7	e 5.08	L 15.0	3.30		3.8 3.6 EUR	3.0	2.6 2.2	ISSUE DATE

Fig 7. Package outline SOD59 (2-lead TO-220AC)

Rectifier diode, hyperfast

8. Revision history

Table 6.	Revision history						
Document	ID	Release date	Data sheet status	Change notice	Supersedes		
BYC20-600	0_1	20071128	Product data sheet	-	-		

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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